



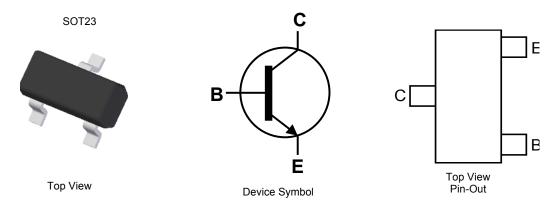
40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23
- Case material: molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



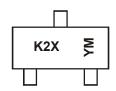
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401-7-F	AEC-Q101	K2X	7	8	3,000
MMBT4401-13-F	AEC-Q101	K2X	13	8	10,000
MMBT4401Q-13-F	Automotive	K2X	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product compliance definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K2X = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: A = 2013) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2010	20	011	2012	2	2013	2014		2015	2016		2017
Code	Х		Υ	Z		Α	В		С	D		Е
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	٧
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	Ic	600	mA
Peak Collector Current	I _{CM}	1	Α
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	310	mW	
Power Dissipation	(Note 7)	P _D	350		
Thermal Resistance, Junction to Ambient	(Note 6)	В	403	°C/M	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	357	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

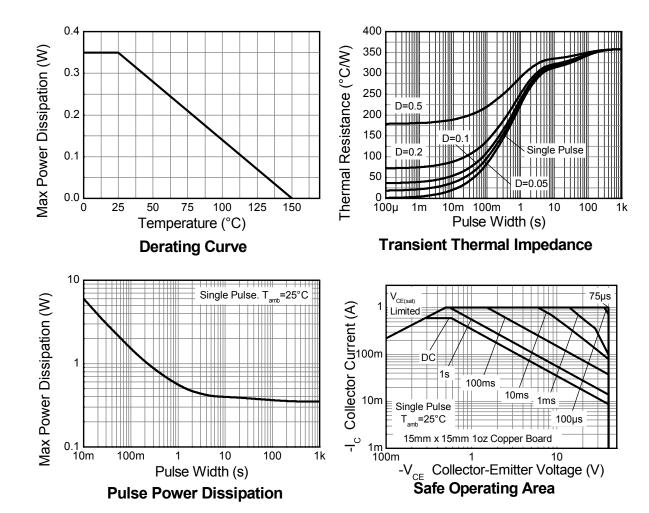
ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air 7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS	-					
Collector-Base Breakdown Voltage	BV_{CBO}	60	_	V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage(Note 10)	BV _{CEO}	40	1	V	$I_C = 10.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	_	V	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$	
Base Cutoff Current	I _{BL}		100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$	
ON CHARACTERISTICS (Note 10)						
DC Current Gain	h _{FE}	20 40 80 100 40	 300 		$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_C &= 10 m A, \ V_{CE} = 1.0 V \\ I_C &= 150 m A, \ V_{CE} = 1.0 V \\ I_C &= 500 m A, \ V_{CE} = 2.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA	
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.75 —	0.95 1.2	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{cb}		6.5	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{eb}	_	30	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$	
Input Impedance	h _{ie}	1.0	15	kΩ	_	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$	
Small Signal Current Gain	h _{fe}	40	500	_	f = 1.0kHz	
Output Admittance	h _{oe}	1.0	30	μS		
Current Gain-Bandwidth Product	f⊤	250		MHz	$V_{CE} = 10V, I_{C} = 20mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _d	_	15	ns	$V_{CC} = 30V, I_{C} = 150mA,$	
Rise Time	t _r	_	20	ns	$V_{BE(off)} = 2.0V, I_{B1} = 15mA$	
Storage Time	ts	_	225	ns	$V_{CC} = 30V, I_{C} = 150mA,$	
Fall Time	t _f	_	30	ns	$I_{B1} = -I_{B2} = 15mA$	

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



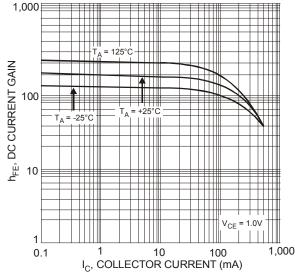


Figure 1 Typical DC Current Gain vs. Collector Current

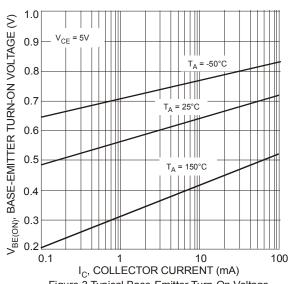


Figure 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

1,000

V_{CE} = 5V

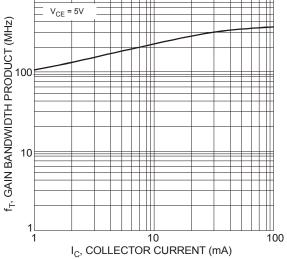


Figure 5 Typical Gain Bandwidth Product vs. Collector Current

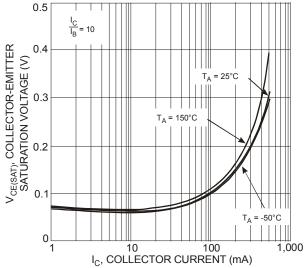


Figure 2 Collector-Emitter Saturation Voltage vs. Collector Current

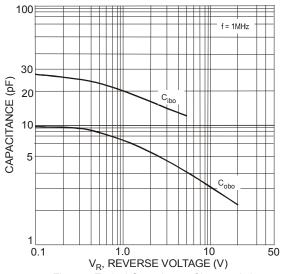


Figure 4 Typical Capacitance Characteristics

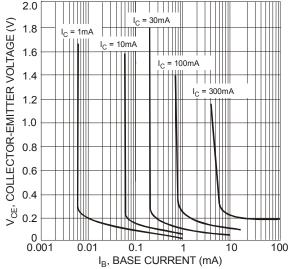
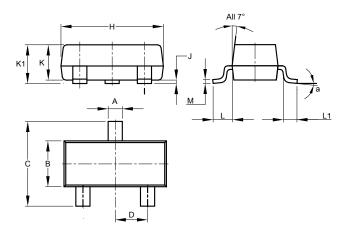


Figure 6 Typical Collector Saturation Region



Package Outline Dimensions

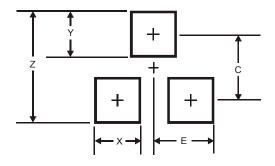
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	8°						
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35



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